- Package form: top view
- Dimensions (L x W x H in mm): 5 x 4.24 x 1.12
- Radiant sensitive area (in mm²): 7.5
- AEC-Q101 qualified
- High radiant sensitivity
- Daylight blocking filter matched with 870 to 950
 AUTOMOTIVE
 GRADE
 nm emitters
- · Fast response times
- Angle of half sensitivity: $\varphi = \pm 65^{\circ}$
- Floor life: 72 h, MSL 4, acc. J-STD-020
- Lead (Pb)-free reflow soldering
- Compliant to RoHS directive 2002/95/EC and in accordance to WEEE 2002/96/EC
- Find out more about Vishay's Automotive Grade Product requirements at: www.vishay.com/applications

APPLICATIONS

- · High speed detector for infrared radiation
- Infrared remote control and free air data transmissionsystems, e.g. in combination with TSFFxxxx series IR emitters

PRODUCT SUMMARY

wavelength 870 nm or 950 nm.

DESCRIPTION

COMPONENT	I _{ra} (μΑ)	φ (deg)	λ _{0.5} (nm)
TEMD5110X01	55	± 65	790 to 1050

Note

Test conditions see table "Basic Characteristics"

ORDERING INFORMATION				
ORDERING CODE	PACKAGING REMARKS		PACKAGE FORM	
TEMD5110X01	Tape and reel	MOQ: 1500 pcs, 1500 pcs/reel	Top view	

Note

MOQ: minimum order quantity

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Reverse voltage		V _R	60	V
Power dissipation	$T_{amb} \le 25 \ ^{\circ}C$	Pv	215	mW
Junction temperature		Tj	100	°C
Operating temperature range		T _{amb}	- 40 to + 100	°C
Storage temperature range		T _{stg}	- 40 to + 110	°C
Soldering temperature	Acc. reflow sloder profile fig. 8	T _{sd}	260	°C
Thermal resistance junction/ambient		R _{thJA}	350	K/W

Note

T_{amb} = 25 °C, unless otherwise specified

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Silicon PIN Photodiode



TEMD5110X01 is a high speed and high sensitive PIN

photodiode. It is a miniature surface mount device (SMD)

including the chip with a 7.5 mm² sensitive area and a daylight blocking filter matched with IR emitters operating at





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(e4) RoHS

TEMD5110X01

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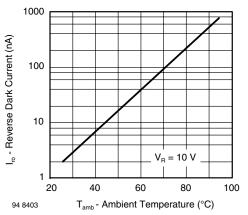
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	I _F = 50 mA	V _F		1	1.3	V
Breakdown voltage	I _R = 100 μA, E = 0	V _(BR)	60			V
Reverse dark current	V _R = 10 V, E = 0	I _{ro}		2	30	nA
Diode capacitance	$V_{R} = 0 V, f = 1 MHz, E = 0$	C _D		70		pF
	V _R = 3 V, f = 1 MHz, E = 0	CD		25	40	pF
Open circuit voltage	$E_e = 1 \text{ mW/cm}^2$, $\lambda = 950 \text{ nm}$	Vo		350		mV
Temperature coefficient of Vo	$E_e = 1 \text{ mW/cm}^2$, $\lambda = 950 \text{ nm}$	TK _{Vo}		- 2.6		mV/K
Short circuit current	$E_e = 1 \text{ mW/cm}^2$, $\lambda = 950 \text{ nm}$	l _k		50		μΑ
Temperature coefficient of I_k	$E_e = 1 \text{ mW/cm}^2$, $\lambda = 950 \text{ nm}$	ΤK _{Ik}		0.1		%/K
Reverse light current	$E_e = 1 \text{ mW/cm}^2, \lambda = 950 \text{ nm}, \\ V_R = 5 \text{ V}$	I _{ra}	45	55		μA
Angle of half sensitivity		φ		± 65		deg
Wavelength of peak sensitivity		λρ		940		nm
Range of spectral bandwidth		λ _{0.5}		790 to 1050		nm
Noise equivalent power	$V_{R} = 10 \text{ V}, \lambda = 950 \text{ nm}$	NEP		4 x 10 ⁻¹⁴		W/√Hz
Rise time	$V_{R} = 10 \text{ V}, \text{R}_{L} = 1 \text{k}\Omega, \\ \lambda = 820 \text{ nm}$	tr		100		ns
Fall time	$V_R = 10 V, R_L = 1 k\Omega,$ $\lambda = 820 nm$	t _f		100		ns

Note

 $T_{amb} = 25 \ ^{\circ}C$, unless otherwise specified

BASIC CHARACTERISTICS

 T_{amb} = 25 °C, unless otherwise specified





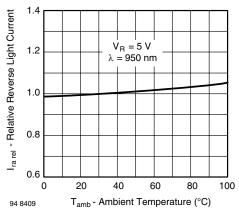


Fig. 2 - Relative Reverse Light Current vs. Ambient Temperature



TEMD5110X01

Silicon PIN Photodiode

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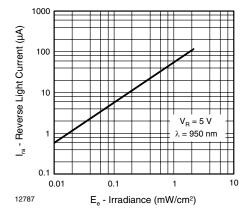


Fig. 3 - Reverse Light Current vs. Irradiance

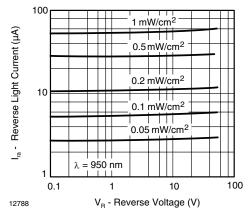


Fig. 4 - Reverse Light Current vs. Reverse Voltage

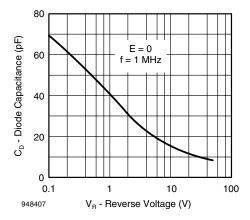


Fig. 5 - Diode Capacitance vs. Reverse Voltage

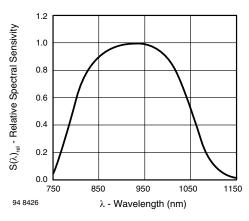


Fig. 6 - Relative Spectral Sensitivity vs. Wavelength

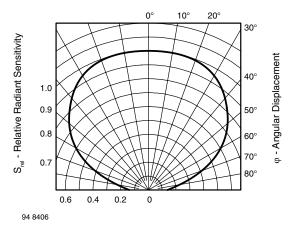


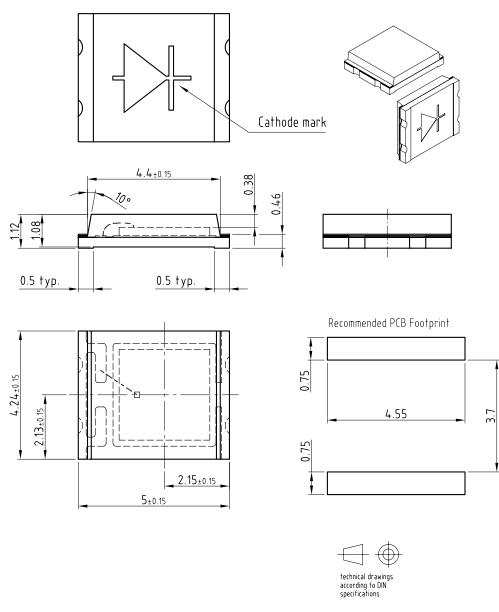
Fig. 7 - Relative Radiant Sensitivity vs. Angular Displacement

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PACKAGE DIMENSIONS in millimeters



Not indicated tolerances ± 0.1

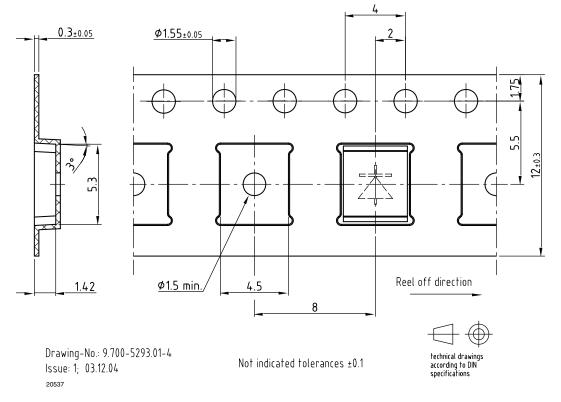
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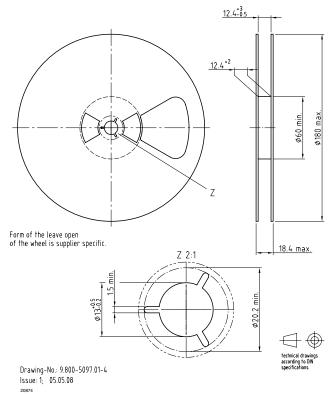
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TAPING DIMENSIONS in millimeters



REEL DIMENSIONS in millimeters



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TEMD5110X01

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SOLDER PROFILE

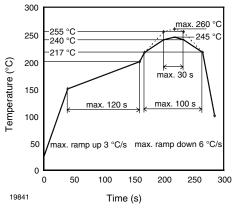


Fig. 8 - Lead (Pb)-free Reflow Solder Profile acc. J-STD-020D

DRYPACK

Devices are packed in moisture barrier bags (MBB) to prevent the products from moisture absorption during transportation and storage. Each bag contains a desiccant.

FLOOR LIFE

Time between soldering and removing from MBB must not exceed the time indicated in J-STD-020: Moisture sensitivity: level 4 Floor life: 72 h Conditions: $T_{amb} < 30$ °C, RH < 60 %

DRYING

In case of moisture absorption devices should be baked before soldering. Conditions see J-STD-020 or recommended conditions: 192 h at 40 °C (+ 5 °C), RH < 5 % or 96 h at 60 °C (+ 5 °C), RH < 5 %.



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